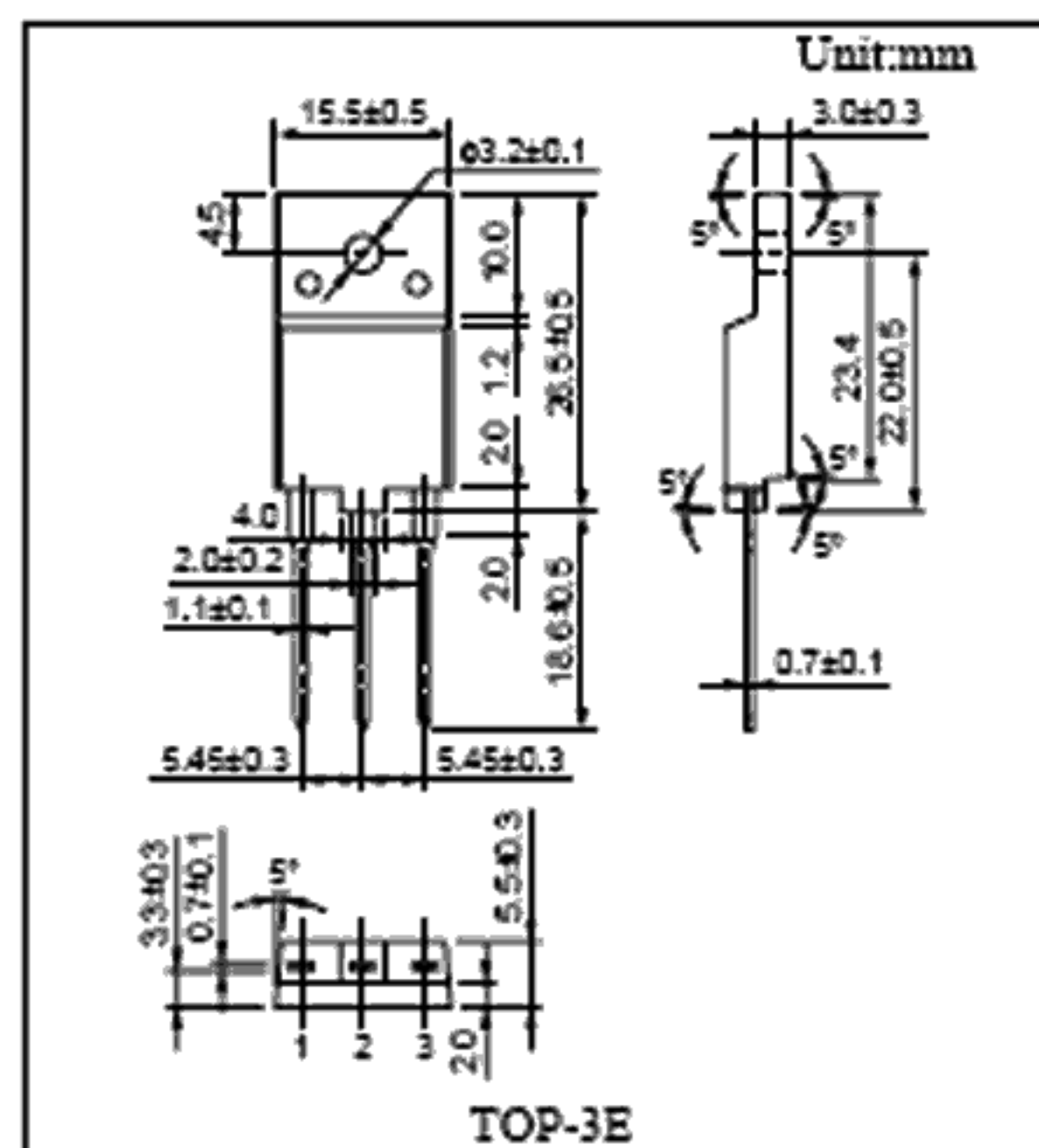


2SC5572

■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	1500	V
Collector to emitter voltage	V _{CES}	1500	V
Emitter to base voltage	V _{EB0}	7	V
Peak collector current	I _{CP}	12 ^{*)}	A
Collector current	I _C	6	A
Base current	I _B	3	A
Collector power dissipation	P _C	40 ^{*)} 3 ^{*)}	W
Junction temperature	T _j	150	°C
Storage temperature		-55 to +150	°C



*1) T_C=25°C, *2) T_a=25°C (Without heat sink)

*3) Non-repetitive peak collector current.

■ Electrical Characteristics (T_C=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I _{CBO}	V _{CB} =1000V, I _E =0	-	-	50	μA
	I _{CBO}	V _{CB} =1500V, I _E =0	-	-	1	mA
Emitter to base voltage	V _{EB0}	I _E =500mA, I _C =0	7	-	-	V
Forward current transfer ratio	f _{FE}	V _{CE} =5V, I _C =4A	5	-	9	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C =4A, I _B =0.8A	-	-	3	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C =4A, I _B =0.8A	-	-	1.5	V
Transition frequency	f _T	V _{CE} =10V, I _C =0.1A, f=0.5MHz	-	3	-	MHz
Storage time	T _{stg}	I _C =4A, I _{B1} =0.8A, I _{B2} =-1.6A	-	-	5.0	μs
Fall time	T _f	I _C =4A, I _{B1} =0.8A, I _{B2} =-1.6A	-	-	0.5	μs
Diode characteristics	V _F	I _F =4A	-	-	-2	V